1. General description

PNP high-voltage low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X-Q

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

3. Applications

- · Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch mode power supply

4. Quick reference data

Table 1. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-400	V
I _C	collector current			-	-	-0.5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-1	Α
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		140	-	450	
R _{CEsat}	collector-emitter saturation resistance	I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C		-	-	2000	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV9540X-Q		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9540X-Q	%4Н

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

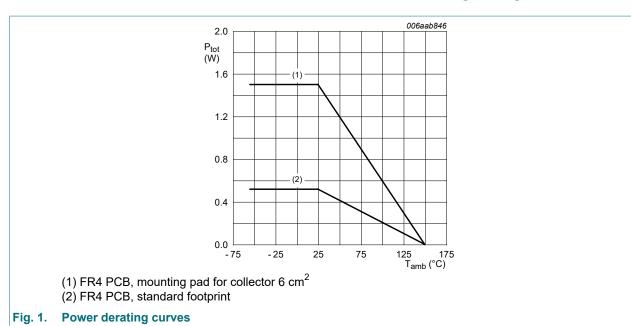
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-400	V
V _{CEO}	collector-emitter voltage	open base		-	-400	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-400	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-0.5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	А
I _B	base current			-	-250	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	240	K/W
junction to a	junction to ambient		[2]	-	-	83	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

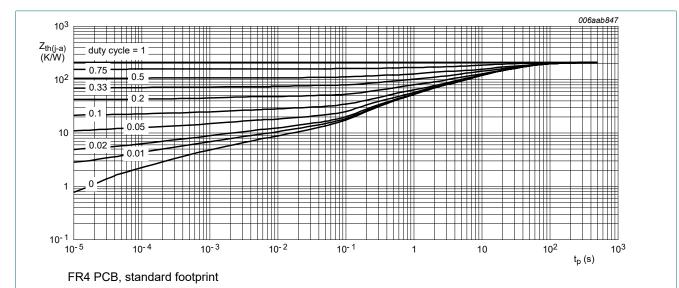
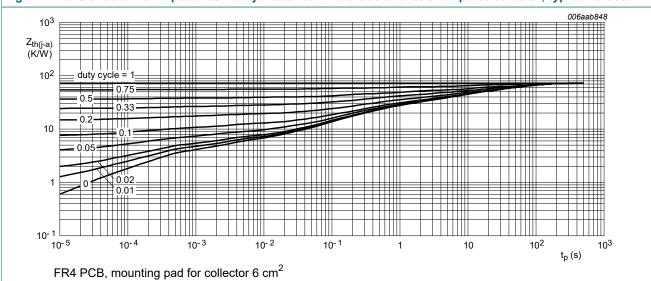


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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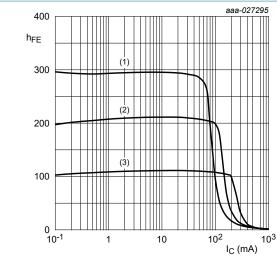
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-400	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = -2.5 mA; I_B = 0 A; T_{amb} = 25 °C	-400	-	-	V
V _{(BR)CES}	collector-emitter breakdown voltage (base shorted)	I_C = -2.5 mA; V_{BE} = 0 V; T_{amb} = 25 °C	-400	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = -100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	-7	-	-	V
I _{CBO}	collector-base cut-off	$V_{CB} = -320 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	V _{CB} = -320 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μΑ
I _{ЕВО}	emitter-base cut-off current	V _{EB} = -7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = -320 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -20 mA; T_{amb} = 25 °C	140	-	450	
		V_{CE} = -5 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	140	-	400	
V _{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	-250	mV
		I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le$	-	-	-400	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	2000	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -100 mA; I_B = -10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	-0.9	V
		I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	-1	V
V_{BE}	base-emitter voltage	V_{CE} = -10 V; I_{C} = -200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	-0.9	V
d	delay time	$V_{CC} = -6.2 \text{ V}; I_C = -100 \text{ mA};$	-	60	-	ns
r	rise time	I_{Bon} = -10 mA; I_{Boff} = 20 mA; T_{amb} = 25 °C	-	3650	-	ns
on	turn-on time	1 amb - 23 C	-	3710	-	ns
t _s	storage time		-	810	-	ns
t _f	fall time		-	900	-	ns
t _{off}	turn-off time		-	1710	-	ns
fт	transition frequency	V_{CE} = -5 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	-	65	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	14	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	235	-	pF

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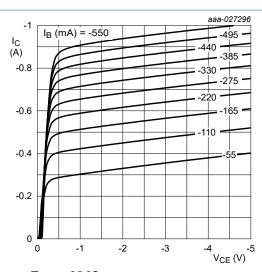
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$$V_{CE} = -5 V$$

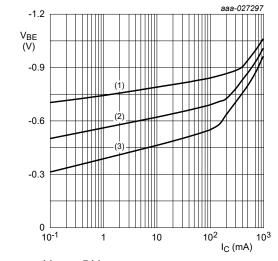
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 V_{CE} = -5 V

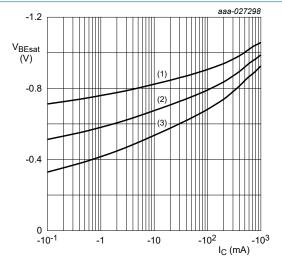
$$(1) T_{amb} = -55 ° C$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

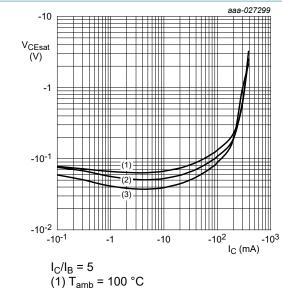
Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

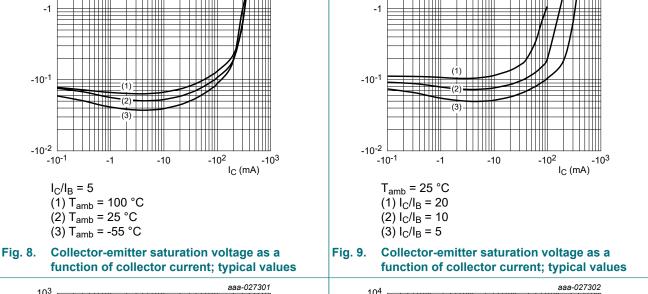
 V_{CEsat}

(V)

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aaa-027300





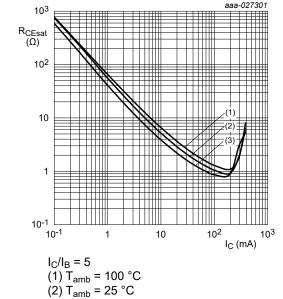


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

(3) $T_{amb} = -55 \, ^{\circ}C$

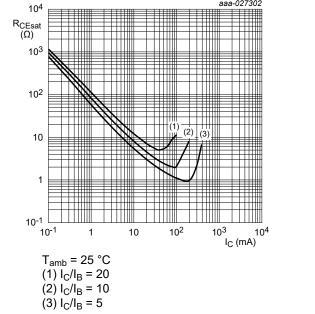
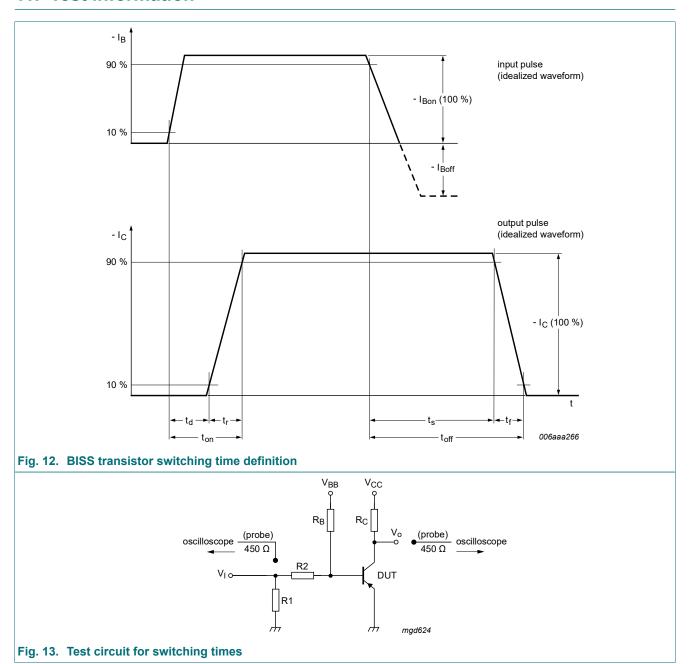


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

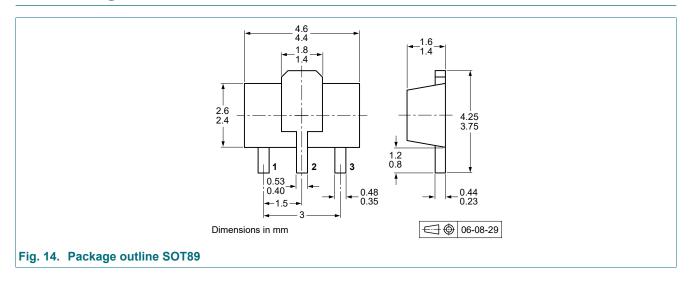


Quality information

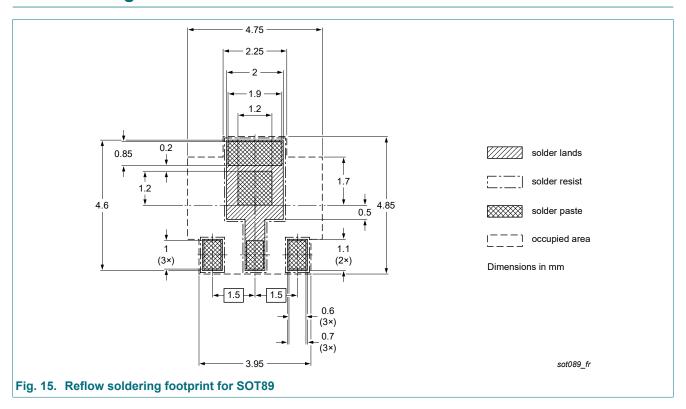
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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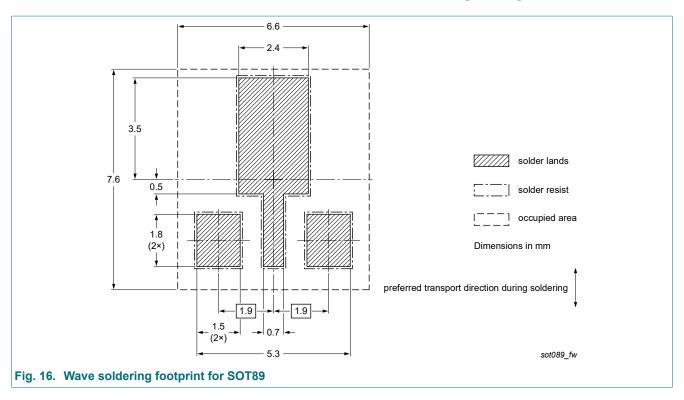
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9540X-Q v.1	20230718	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 18 July 2023

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